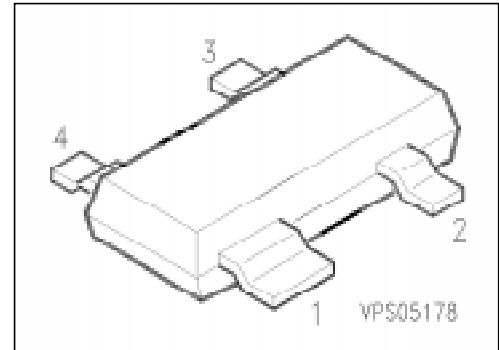


Silicon Switching Diode Array

BGX 50 A

- Bridge configuration
- High-speed switch diode chip



Type	Marking	Ordering Code (tape and reel)	Pin Configuration	Package ¹⁾
BGX 50 A	U1s	Q62702-G38		SOT-143

Maximum Ratings per Diode

Parameter	Symbol	Values	Unit
Reverse voltage	V_R	50	V
Peak reverse voltage	V_{RM}	70	
Forward current	I_F	140	mA
Total power dissipation, $T_s = 74\text{ °C}$	P_{tot}	210	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	- 65 ... + 150	

Thermal Resistance

Junction - ambient ²⁾	$R_{th\ JA}$	≤ 640	K/W
Junction - soldering point	$R_{th\ JS}$	≤ 360	

¹⁾ For detailed information see chapter Package Outlines.

²⁾ Package mounted on epoxy pcb 40 mm × 40 mm × 1.5 mm/6 cm² Cu.

Electrical Characteristics

at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

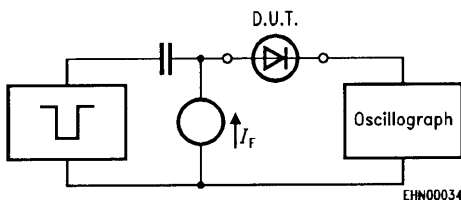
DC characteristics

Forward voltage per diode $I_F = 100\text{ mA}$	V_F	–	–	1.3	V
Reverse current per diode $V_R = 50\text{ V}$ $V_R = 50\text{ V}, T_A = 150\text{ }^\circ\text{C}$	I_R	–	–	0.2 100	μA

AC characteristics

Diode capacitance $V_R = 0, f = 1\text{ MHz}$	C_D	–	–	1.5	pF
Reverse recovery time $I_F = 10\text{ mA}, I_R = 10\text{ mA}, R_L = 100\text{ }\Omega$ measured at $I_R = 1\text{ mA}$	t_{rr}	–	–	6	ns

Test circuit for reverse recovery time

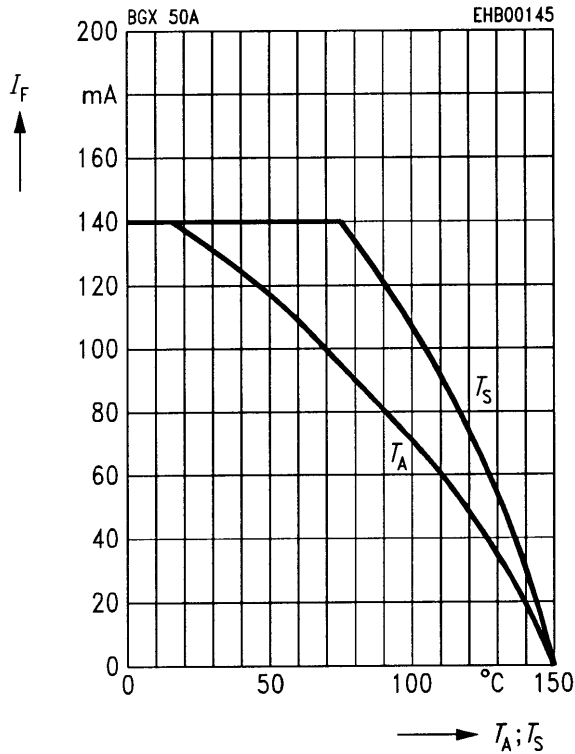


Pulse generator: $t_p = 100\text{ ns}, D = 0.05$
 $t_r = 0.6\text{ ns}, R_j = 50\text{ }\Omega$

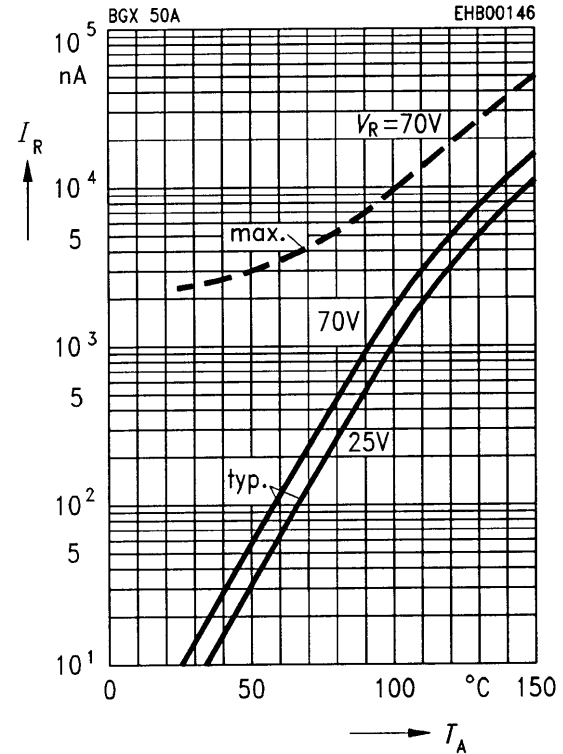
Oscilloscope: $R = 50\text{ }\Omega$
 $t_r = 0.35\text{ ns}$
 $C \leq 1\text{ pF}$

Forward current $I_F = f(T_A^*; T_S)$

* Package mounted on epoxy

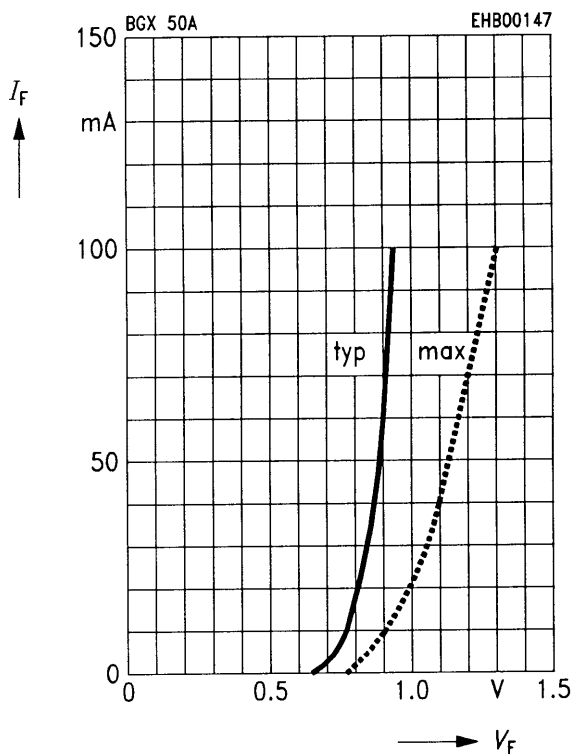


Reverse current $I_R = f(T_A)$



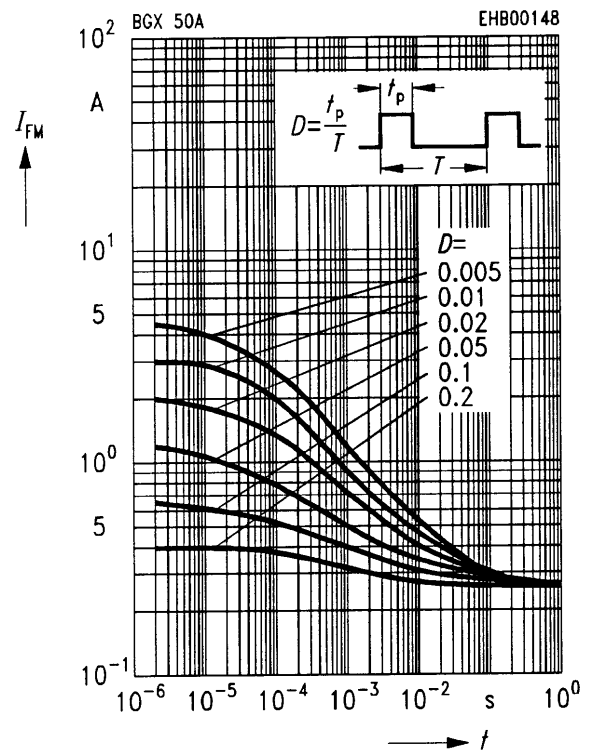
Forward current $I_F = f(V_F)$

$T_A = 25^\circ\text{C}$



Peak forward current $I_{FM} = f(t)$

$T_A = 25^\circ\text{C}$



Forward voltage $V_F = f(T_A)$

